

GR-20E007DJ: E-mode GaN Power Transistor

Description

GR-20E007DJ is an enhancement mode GaN on Silicon power transistor. 20E007DJ provides, high current and high operating speed which is suitable for DC to DC power supply applications.

Key Specifications

Part Number	GR-20E007DJ
V _{DSS} , min.	200V
I _{DS} , Pulse((25°C, TPULSE = 300 μs))	125A
R _{DS(ON)} , typ. @V _{gs} =5V	7.3mΩ
Q _G , typ.	10.6nC

Features

- 200 V enhancement mode power transistor
- High operating frequency
- R_{DS(on)} = Typ. 7.3mΩ
- RoHS compliant
- Zero QRR.

Applications

- Switch Mode Power Supplies (SMPS)
- DC-DC Converters
- Fast Battery Charging
- Appliance Motor Drives

